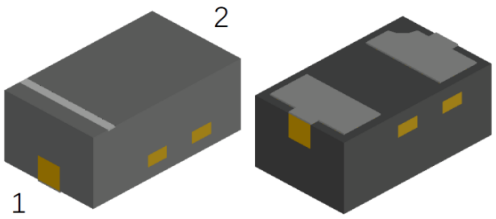
Schottky Barrier Diode

Parameter	Value	Unit
V_{RRM}	70	V
$I_{F(AV)}$	70	mA

DFN1006-2L





Features

- Moisture sensitivity level 3
- Reverse voltage: 70V
- Average forward current: 70mA

Applications

- Low forward Voltage
- Fast switching

Absolute Maximum Ratings(Ta=25℃unless otherwise noted)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	70	V
Maximum average forward rectified current	$I_{F(AV)}$	70	mA
Non-repetitive Peak Forward Surge Current @t=8.3ms Half-sine wave	I_{FSM}	100	mA
Non-repetitive surge peak forward current@t=1ms square wave			
Repetitive Peak Forward Current @ tp=1ms, δ=0.25	I_{FRM}	70	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	-55 ~+125	℃
Storage temperature range	T_{STG}	-55 ~+150	℃
Thermal Resistance Junction-ambient [1]	$R_{\theta JA}$	667	℃/W
Thermal Resistance Junction-case [1]	$R_{\theta JC}$	534	℃/W

Note:
1.Thermal resistance from junction to ambient and from junction to case mounted on P.C.B. with 17mm*10mm copper pad areas.

Electrical Characteristics(Ta=25℃unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse voltage	V_R	I_R=10uA	70	--	--	V
Maximum forward voltage	V_F	I_F=1mA	--	--	410	mV
		I_F=15mA	--	--	1000	
Maximum reverse current	I_R	V_R=50V	--	--	0.2	μA
Capacitance between terminals	C_T	V_R=1V, f=1MHz	--	--	2	pF
Maximum reverse recovery time	T_{rr}	I_F=I_R=10mA, Irr=0.1*IR, R_L=100Ω	--	--	5	ns

Typical Characteristics

Fig 1：P_D-Ta Curve

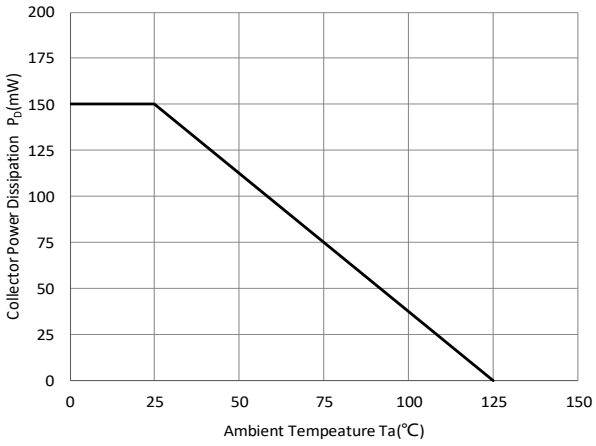


Fig 2：Capacitance Capability

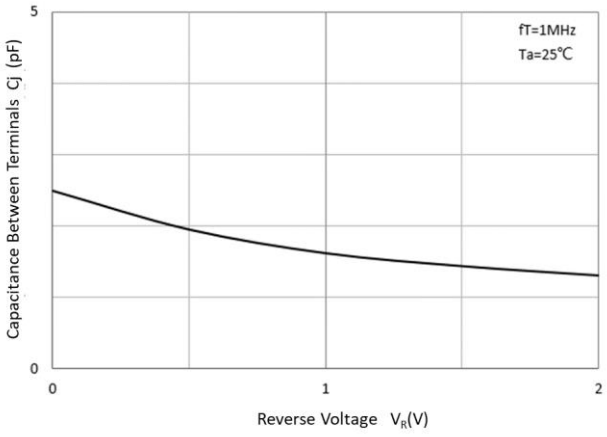


Fig 3：Typical Forward Characteristics

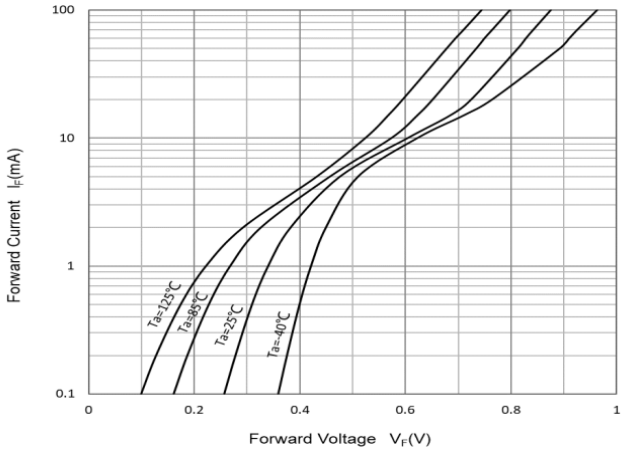
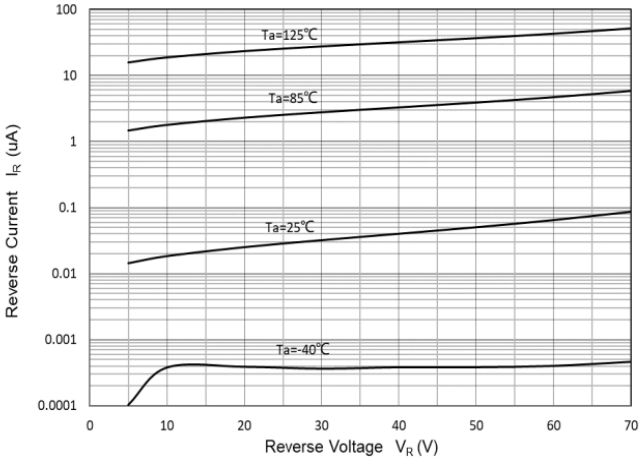
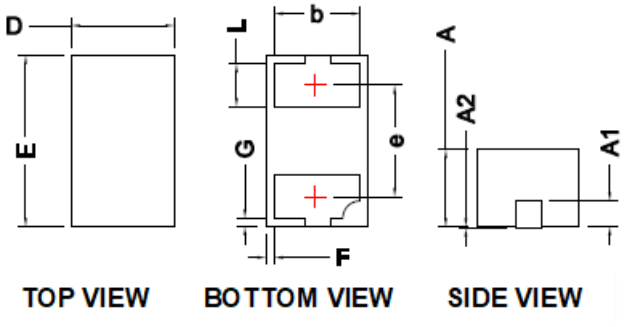


Fig 4：Typical Reverse Characteristics

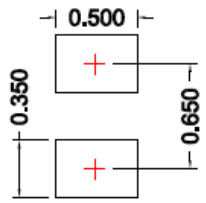


Package Outline
DFN1006-2L



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	0.50	0.60	0.70
E	0.90	1.00	1.10
A	0.35	0.45	0.55
A1		0.15 BSC	
A2			0.10
F	0.005		
G	0.005		
L	0.15	0.25	0.35
b	0.41	0.50	0.59
e		0.65 BSC	

■ **Suggested Pad Layout**



UNIT：mm

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